

InGaAs - Laser Diode 1000 mW

Wavelength 940 nm, chip on carrier

Data differing from SFH 48 0402 and SFH 48 0403:

Characteristic Data:				
Parameter:	Typical Values		Unit	Condition
Lambda	940 +/- 10		nm	DC, 1W
FWHM	4		nm	
Ith	450		mA	
eta	0,8		W/A	in NA=0,6
Iop(1W)	1700	<2000	mA	in NA=0,6
Uop(1W)	2100	<2500	mV	
Rs	2100	<0,5	Ohm	
TCLambda	0,3	0,35	nm/K	temperature coefficient of wavelength
TCI	1		%/K	temperature coefficient of operation current
Maximum Ratings:				
cw-output power	1050		mW	
operating temperature	-10 ... +40°C		°C	bedewing is excluded
reverse voltage	1		V	